Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK2009

High Speed Switching Applications Analog Switch Applications

- High input impedance.
- Low gate threshold voltage: $V_{th} = 0.5 \sim 1.5 \text{ V}$
- Excellent switching times: $t_{on} = 0.06 \mu s$ (typ.)

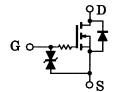
 $t_{off} = 0.12 \mu s \text{ (typ.)}$

- Low drain-source ON resistance: RDS (ON) = 1.2Ω (typ.)
- · Small package.
- Enhancement-mode

Marking

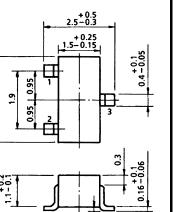






Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	30	V
Gate-source voltage	V_{GSS}	±20	V
DC drain current	ID	200	mA
Drain power dissipation	P_{D}	200	mW
Channel temperature	T _{ch}	150	°C
Storage temperature range	T _{stg}	-55~150	°C



S-MINI 2. SOURCE 3. DRAIN

JEDEC	TO-236MOD	
JEITA	SC-59	
TOSHIBA	2-3F1F	

1. GATE

Weight: 0.012 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

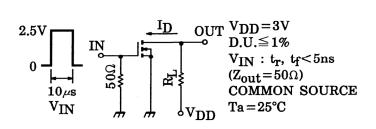
Note: This transistor is electrostatic sensitive device. Please handle with caution.

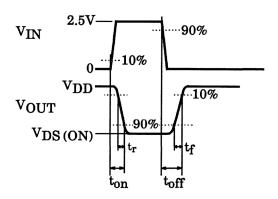


Electrical Characteristics (Ta = 25°C)

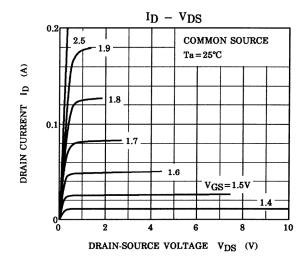
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$	_	_	±0.1	μΑ
Drain-source breakdown voltage		V _{(BR) DSS}	$I_D = 1$ mA, $V_{GS} = 0$	30	_	_	V
Drain cut-off curre	ent	I _{DSS}	$V_{DS} = 30 \ V, \ V_{GS} = 0$	_	_	10	μА
Gate threshold vo	Itage	V _{th}	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	0.5	_	1.5	V
Forward transfer a	admittance	Y _{fs}	$V_{DS} = 3 \text{ V}, I_D = 50 \text{ mA}$	100	_	_	mS
Drain-source ON	resistance	R _{DS} (ON)	$I_D = 50$ mA, $V_{GS} = 2.5$ V	_	1.2	2	Ω
Input capacitance		C _{iss}	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	70	_	pF
Reverse transfer of	capacitance	C _{rss}	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	23	_	pF
Output capacitano	e	Coss	V _{DS} = 3 V, V _{GS} = 0, f = 1 MHz	_	58	_	pF
Switching time	Turn-on time	t _{on}	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}, V_{GS} = 0~2.5 \text{ V}$	_	0.06	_	μS
	Turn-off time	t _{off}	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}, V_{GS} = 0~2.5 \text{ V}$	_	0.12	_	

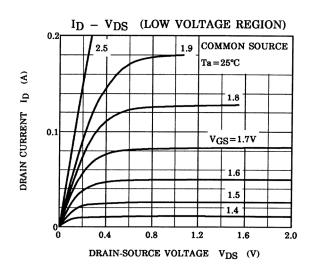
Switching Time Test Circuit

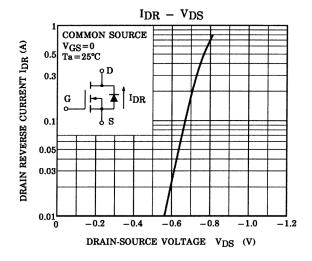


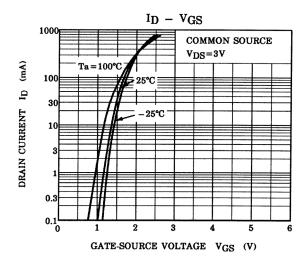


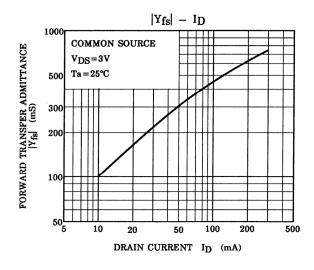
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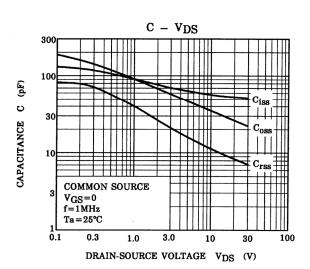


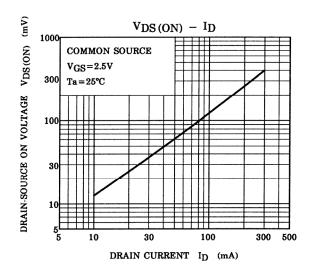


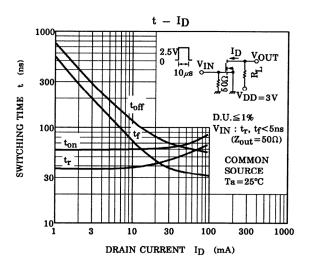


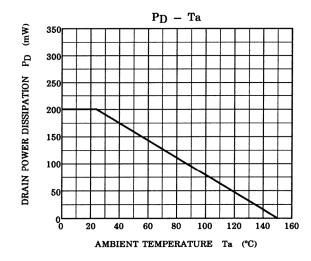












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20070701-EN GENERAL

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